

GLBCP69 PNP SILICON EPITAXIAL TRANSISTOR

Description

The GLBCP69 is designed for use in low voltage and medium power applications.

Features

- $V_{CE0} : -20V$
- $I_C : 1A$

Package Dimensions

SOT-223

Marking :

Date Code →

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.70	7.30	B	13° TYP.	
C	2.90	3.10	J	2.30 REF.	
D	0.02	0.10	1	6.30	6.70
E	0°	10°	2	6.30	6.70
I	0.60	0.80	3	3.30	3.70
H	0.25	0.35	4	3.30	3.70
			5	1.40	1.80

Absolute Maximum Ratings at $T_a = 25^\circ C$

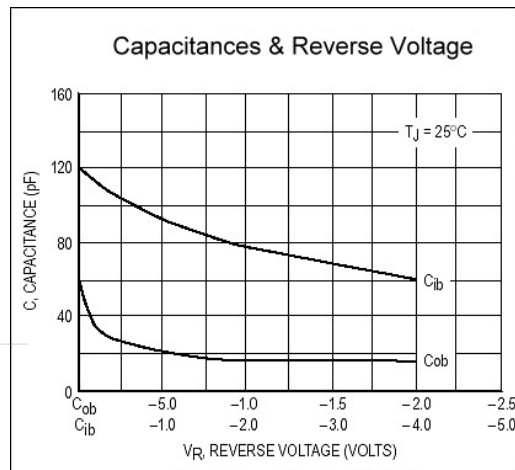
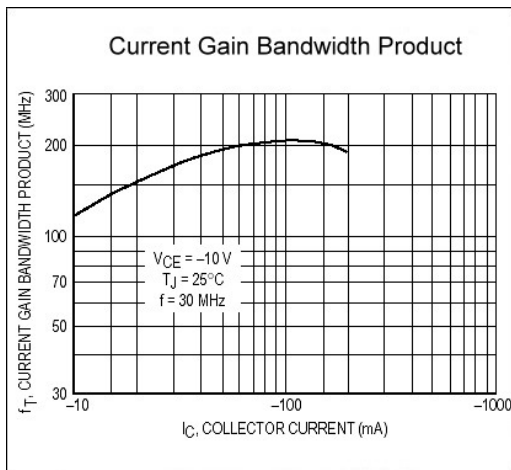
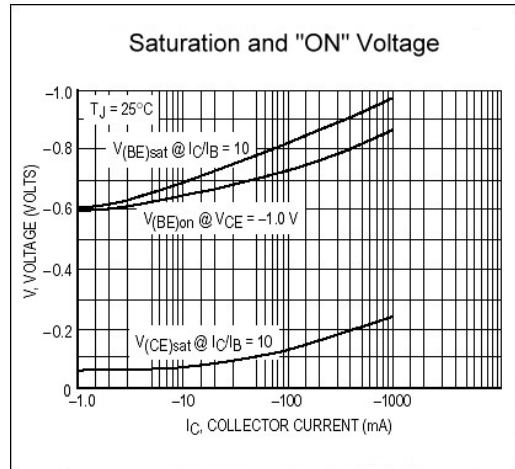
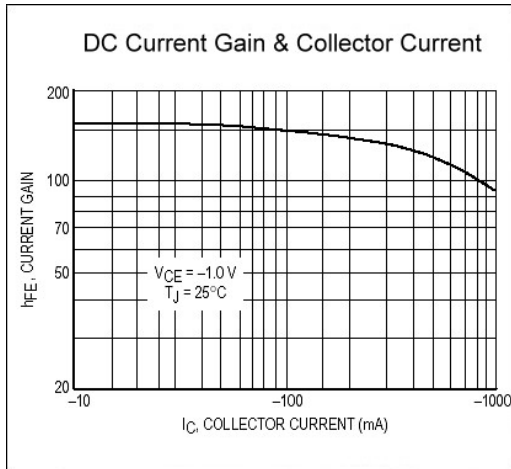
Parameter	Symbol	Ratings	Unit
Junction Temperature	T_j	+150	$^\circ C$
Storage Temperature	T_{stg}	-65~+150	$^\circ C$
Collector to Base Voltage	V_{CB0}	-25	V
Collector to Emitter Voltage	V_{CE0}	-20	V
Emitter to Base Voltage	V_{EB0}	-5	V
Collector Current	I_C	-1	A
Total Power Dissipation	P_D	1.5	W

Electrical Characteristics ($T_a = 25^\circ C$, unless otherwise noted)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CB0}	-25	-	-	V	$I_C = -100\mu A, I_E = 0$
BV_{CE0}	-20	-	-	V	$I_C = -1mA, I_B = 0$
BV_{EB0}	-5	-	-	V	$I_E = -10\mu A, I_C = 0$
I_{CB0}	-	-	-10	μA	$V_{CB} = -25V, I_E = 0$
I_{EB0}	-	-	-10	μA	$V_{EB} = -5V, I_C = 0$
* $V_{CE(sat)1}$	-	-	-500	mV	$I_C = -1A, I_B = -100mA$
* $V_{BE(on)}$	-	-	-1.0	V	$V_{CE} = -1V, I_C = -1A$
* h_{FE1}	50	-	-	-	$V_{CE} = -10V, I_C = -5mA$
* h_{FE2}	85	-	375	-	$V_{CE} = -1V, I_C = -500mA$
* h_{FE3}	60	-	-	-	$V_{CE} = -1V, I_C = -1A$
fT	-	60	-	MHz	$V_{CE} = -5V, I_C = -10mA$

*Pulse Test: Pulse Width $\leq 380\mu s$, Duty Cycle $\leq 2\%$

Characteristics Curve



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